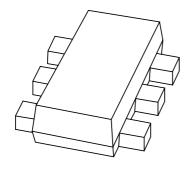
DISCRETE SEMICONDUCTORS

DATA SHEET



BC847BVN NPN/PNP general purpose transistor

Product data sheet Supersedes data of 2001 Aug 30 2001 Nov 07



NPN/PNP general purpose transistor

BC847BVN

FEATURES

- 300 mW total power dissipation
- Very small 1.6 mm x 1.2 mm ultra thin package
- Excellent coplanarity due to straight leads
- Replaces two SC-75/SC-89 packaged transistors on same PCB area
- · Reduced required PCB area
- Reduced pick and place costs.

APPLICATIONS

- · General purpose switching and amplification
- Switch mode power supply complementary MOSFET driver
- · Complementary driver for audio amplifiers.

DESCRIPTION

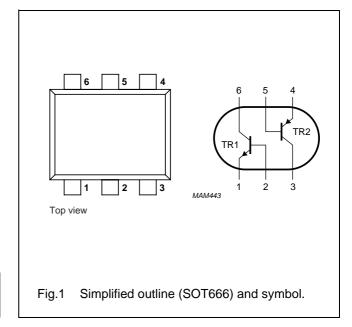
NPN/PNP transistor pair in a SOT666 plastic package.

MARKING

TYPE NUMBER	MARKING CODE		
BC847BVN	13		

PINNING

PIN	DESCRIPTION		
1, 4	emitter	TR1; TR2	
2, 5	base	TR1; TR2	
6, 3	collector	TR1; TR2	



LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 60134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT	
Per transis	Per transistor; for the PNP transistor with negative polarity					
V _{CBO}	collector-base voltage	open emitter	-	50	V	
V _{CEO}	collector-emitter voltage	open base	_	45	V	
V _{EBO}	emitter-base voltage	open collector	-	5	٧	
I _C	collector current (DC)		-	100	mA	
I _{CM}	peak collector current		_	200	mA	
I _{BM}	peak base current		-	200	mA	
P _{tot}	total power dissipation	T _{amb} ≤ 25 °C; note 1	-	200	mW	
T _{stg}	storage temperature		-65	+150	°C	
Tj	junction temperature		-	150	°C	
T _{amb}	operating ambient temperature		-65	+150	°C	
Per device	Per device					
P _{tot}	total power dissipation	T _{amb} ≤ 25 °C; note 1	-	300	mW	

Note

1. Transistor mounted on an FR4 printed-circuit board.

NPN/PNP general purpose transistor

BC847BVN

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT	
R _{th j-a}	thermal resistance from junction to ambient	notes 1 and 2	416	K/W	

Notes

- 1. Transistor mounted on an FR4 printed-circuit board.
- 2. The only recommended soldering is reflow soldering.

CHARACTERISTICS

 T_{amb} = 25 °C unless otherwise specified.

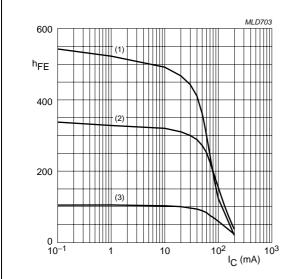
SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
Per transis	Per transistor; for the PNP transistor with negative polarity					
I _{CBO}	collector-base cut-off current	V _{CB} = 30 V; I _E = 0	_	_	15	nA
		$V_{CB} = 30 \text{ V}; I_E = 0; T_j = 150 ^{\circ}\text{C}$	_	_	5	μΑ
I _{EBO}	emitter-base cut-off current	$V_{EB} = 5 \text{ V}; I_{C} = 0$	_	_	100	nA
h _{FE}	DC current gain	$V_{CE} = 5 \text{ V}; I_{C} = 2 \text{ mA}$	200	_	450	
V_{CEsat}	collector-emitter saturation	$I_C = 10 \text{ mA}; I_B = 0.5 \text{ mA}$	_	_	100	mV
	voltage	$I_C = 100 \text{ mA}; I_B = 5 \text{ mA}; \text{ note 1}$	_	_	300	mV
V _{BEsat}	collector-emitter saturation voltage	$I_C = 10 \text{ mA}; I_B = 0.5 \text{ mA}$	_	755	_	mV
f _T	transition frequency	I _C = 10 mA; V _{CE} = 5 V; f = 100 MHz	100	_	_	MHz
NPN trans	NPN transistor					
V _{BE}	base-emitter turn-on voltage	V _{CE} = 5 V; I _C = 2 mA	580	655	700	mV
C _c	collector capacitance	$V_{CB} = 10 \text{ V}; I_E = I_e = 0; f = 1MHz$	_	_	1.5	pF
C _e	emitter capacitance	$V_{EB} = 500 \text{ mV}; I_C = I_c = 0; f = 1MHz$	_	11	_	pF
PNP transistor						
V _{BE}	base-emitter turn-on voltage	$V_{CE} = -5 \text{ V}; I_{C} = -2 \text{ mA}$	600	655	750	mV
C _c	collector capacitance	$V_{CB} = -10 \text{ V}; I_C = I_c = 0; f = 1MHz$	_	_	2.2	pF
C _e	emitter capacitance	$V_{EB} = -500 \text{ mV}; I_E = I_e = 0; f = 1MHz$	_	10	_	pF

Note

1. Pulse test: $t_p \le 300~\mu s;~\delta \le 0.02.$

NPN/PNP general purpose transistor

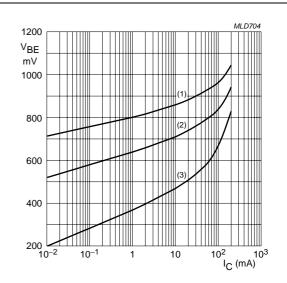
BC847BVN



TR1 (NPN); $V_{CE} = 5 \text{ V}$.

- (1) $T_{amb} = 150 \, ^{\circ}C$.
- (2) $T_{amb} = 25 \, ^{\circ}C$.
- (3) $T_{amb} = -55 \, ^{\circ}C$.

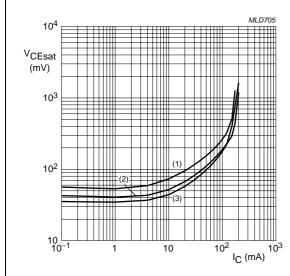
Fig.2 DC current gain as a function of collector current: typical values.



TR1 (NPN); $V_{CE} = 5 \text{ V}$.

- (1) $T_{amb} = -55 \, ^{\circ}C$.
- (2) $T_{amb} = 25 \, ^{\circ}C$.
- (3) $T_{amb} = 150 \, ^{\circ}C$.

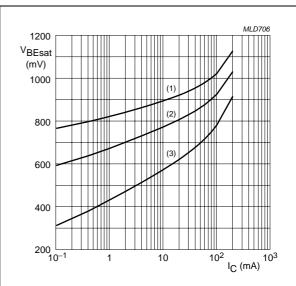
Fig.3 Base-emitter voltage as a function of collector current; typical values.



TR1 (NPN); $I_C/I_B = 20$.

- (1) $T_{amb} = 150 \, ^{\circ}C$.
- (2) $T_{amb} = 25 \, ^{\circ}C$.
- (3) $T_{amb} = -55 \, ^{\circ}C$.

Fig.4 Collector-emitter saturation voltage as a function of collector current: typical values.



TR1 (NPN); $I_C/I_B = 20$.

- (1) $T_{amb} = -55 \, ^{\circ}C$.
- (2) $T_{amb} = 25 \, ^{\circ}C$.

4

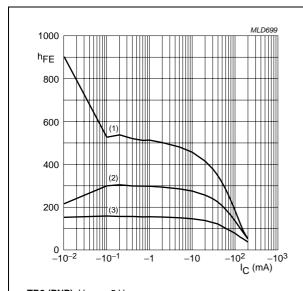
(3) $T_{amb} = 150 \, ^{\circ}C$.

Fig.5 Base-emitter saturation voltage as a function of collector current.

2001 Nov 07

NPN/PNP general purpose transistor

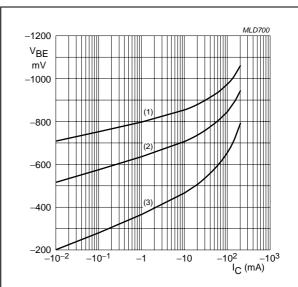
BC847BVN



TR2 (PNP); $V_{CE} = -5 \text{ V}$.

- (1) T_{amb} = 150 °C.
- (2) $T_{amb} = 25 \, ^{\circ}C$.
- (3) $T_{amb} = -55$ °C.

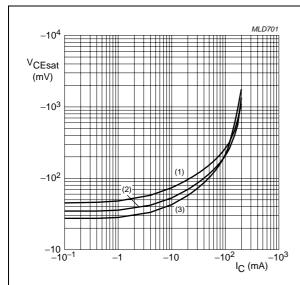
Fig.6 DC current gain as a function of collector current: typical values.



TR2 (PNP); $V_{CE} = -5 \text{ V}$.

- (1) $T_{amb} = -55 \, ^{\circ}C$.
- (2) $T_{amb} = 25 \, ^{\circ}C$.
- (3) $T_{amb} = 150 \, ^{\circ}C$.

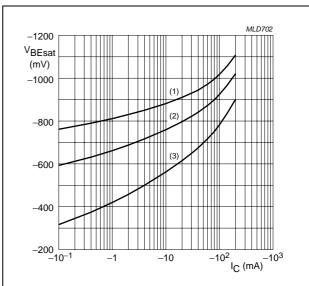
Fig.7 Base-emitter voltage as a function of collector current; typical values.



TR2 (PNP); $I_C/I_B = 20$.

- (1) $T_{amb} = 150 \, ^{\circ}C$.
- (2) $T_{amb} = 25 \, ^{\circ}C$.
- (3) $T_{amb} = -55 \, ^{\circ}C$.

Fig.8 Collector-emitter saturation voltage as a function of collector current: typical values.



TR2 (PNP); $I_C/I_B = 20$.

- (1) $T_{amb} = -55 \, ^{\circ}C$.
- (2) $T_{amb} = 25 \, ^{\circ}C$.
- (3) $T_{amb} = 150 \, ^{\circ}C$.

Fig.9 Base-emitter saturation voltage as a function of collector current.

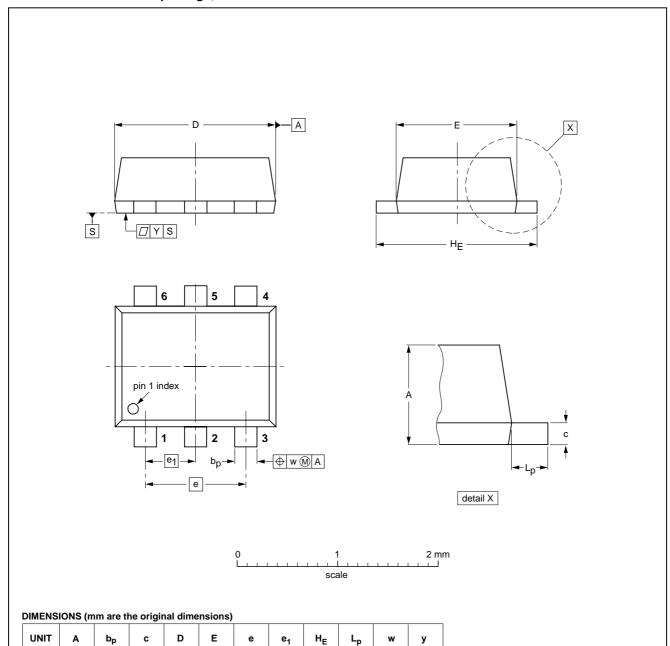
NPN/PNP general purpose transistor

BC847BVN

PACKAGE OUTLINE

Plastic surface mounted package; 6 leads

SOT666



OUTLINE	REFERENCES			EUROPEAN	ISSUE DATE	
VERSION	IEC	JEDEC	EIAJ		PROJECTION	ISSUE DATE
SOT666						-01-01-04 01-08-27

0.3

0.1

2001 Nov 07 6

1.3 1.1

1.0

0.5

0.6 0.5

mm

0.27

0.18

1.7

NPN/PNP general purpose transistor

BC847BVN

DATA SHEET STATUS

DOCUMENT STATUS ⁽¹⁾	PRODUCT STATUS ⁽²⁾	DEFINITION
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Preliminary data sheet	Qualification	This document contains data from the preliminary specification.
Product data sheet	Production	This document contains the product specification.

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